

DCR2880B65



Phase Control Thyristor

DS5786-4 April 2013 (LN30262)

FEATURES

- **Double Side Cooling**
- **High Surge Capability**

KEY PARAMETERS

V _{DRM}	6500V
I _{T(AV)}	2845A
I _{TSM}	38500A
dV/dt*	1500V/µs
dl/dt	300A/µs

* Higher dV/dt selections available

Outline type code: B

(See Package Details for further information)

Fig. 1 Package outline

APPLICATIONS

- **High Power Drives**
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR2880B65* DCR2880B60 DCR2880B55 DCR2880B50	6500 6000 5500 5000	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 300 \text{mA}, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 \text{ms}, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ + 100 \text{V} \\ \text{respectively} \end{array}$

Lower voltage grades available. *6200V @ -40°C, 6500V@ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR2880B65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.





CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	2845	А
I _{T(RMS)}	RMS value	-	4469	А
Ι _Τ	Continuous (direct) on-state current	-	4130	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	38.85	kA
l ² t	I ² t for fusing	$V_R = 0$	7.55	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	s	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.007	°C/W
		Single side cooled	Anode DC	-	0.0116	°C/W
			Cathode DC	-	0.0181	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 76.0kN	Double side	-	0.0014	°C/W
		(with mounting compound)	Single side	-	0.0028	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			68.0	84.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{\text{T(AV)}}$	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω, t _r < 0.5μs, T _j = 125°C	Non-repetitive	-	300	A/µs
V _{T(TO)}	Threshold voltage – Low level	500 to 2400A at T _{case} = 125°	С	-	0.94	V
	Threshold voltage – High level	2400 to 7200A at T _{case} = 125°C		-	1.13	V
r⊤	On-state slope resistance – Low level	500A to 2400A at T _{case} = 125°C		-	0.343	mΩ
	On-state slope resistance – High level	2400A to 7200A at T _{case} = 125°C		-	0.264	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5 \mu$ s, $T_j = 25^{\circ}$ C		-	3	μs
t _q	Turn-off time	$T_{j} = 125^{\circ}C, V_{R} = 200V, dI/dt = 1A/\mu s,$ $dV_{DR}/dt = 20V/\mu s \text{ linear}$		-	1200	μs
Qs	Stored charge	$I_T = 2000A$, $T_j = 125^{\circ}C$, $dI/dt - 1A/\mu s$,		2800	6400	μC
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ι _Η	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I _T = 5A	-	300	mA



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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM,} T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	400	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM,} T _{case} = 125°C	10	mA

CURVES

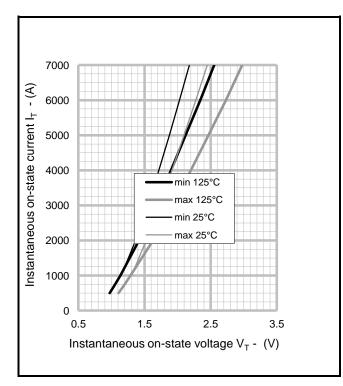


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.914146
B = -0.03808
C = 0.00016
D = 0.015311
these values are valid for
$$T_j$$
 = 125°C for I_T 500A to 7200A



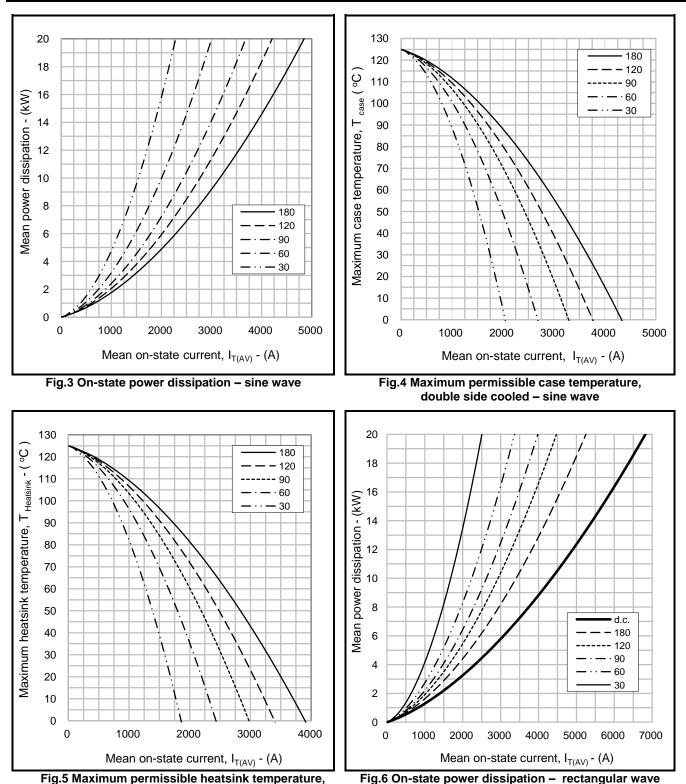


Fig.6 On-state power dissipation - rectangular wave

double side cooled - sine wave

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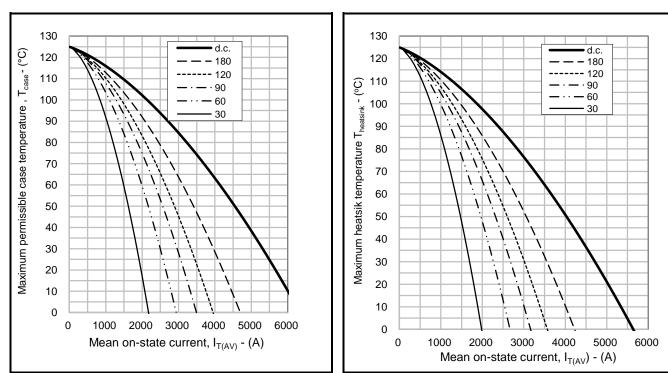


Fig.7 Maximum permissible case temperature, double side cooled - rectangular wave

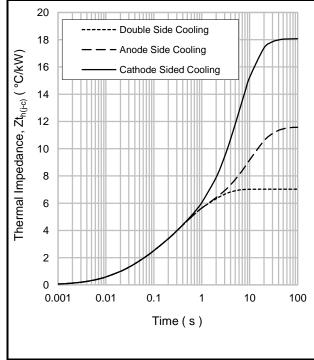


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side cooled	R _i (°C/kW)	0.502	1.333	2.9559	2.2335
	T _i (s)	0.0137081	0.0548877	0.3311925	1.6905
Anode side cooled	R _i (°C/kW)	1.3035	3.138	1.1859	5.9136
	T _i (s)	0.0251065	0.2410256	1.0806	11.002
Cathode side cooled	R _i (°C/kW)	1.2616	2.6216	13.3603	0.8304
	T _i (s)	0.0245837	0.2005035	5.7854	16.765

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$ [1]

$\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance $\mathsf{R}_{\mathsf{th}(j\text{-}c)}$ when the device operates at conduction angles other than d.c.

	Double side cooling				Anode Side	Cooling
	ΔZ_{th}	(z)			ΔZ	_{th} (z)
θ°	sine.	rect.		θ°	sine.	rect.
180	0.70	0.48		180	0.67	0.47
120	0.80	0.68		120	0.77	0.66
90	0.90	0.78		90	0.87	0.75
60	1.00	0.89		60	0.95	0.86
30	1.07	1.01		30	1.02	0.96
15	1.10	1.07		15	1.05	1.02

ΙI	Cathode Sided Cooling		
		ΔZ_{tt}	, (z)
II	θ°	sine.	rect.
	180	0.67	0.47
	120	0.77	0.66
	90	0.87	0.76
	60	0.95	0.86
	30	1.02	0.96
I	15	1.05	1.02

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Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)



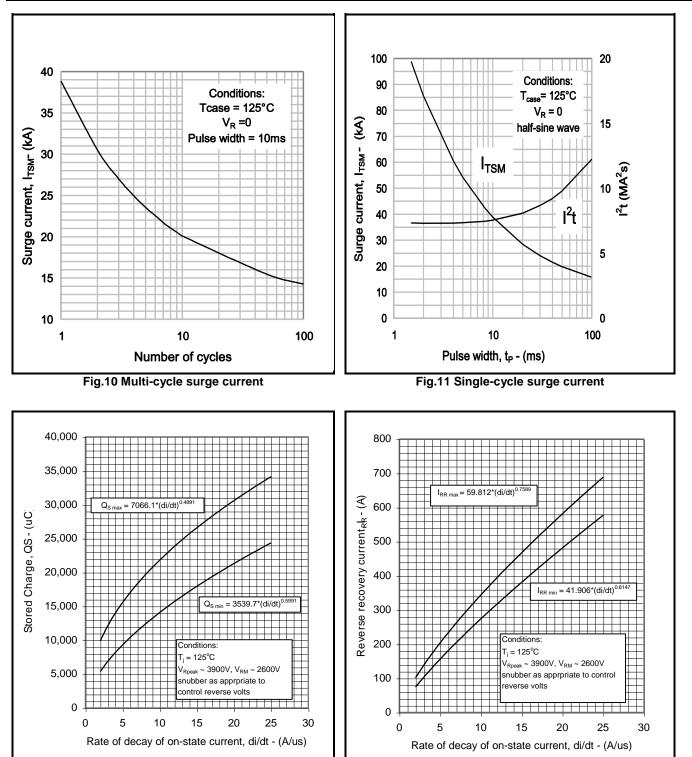
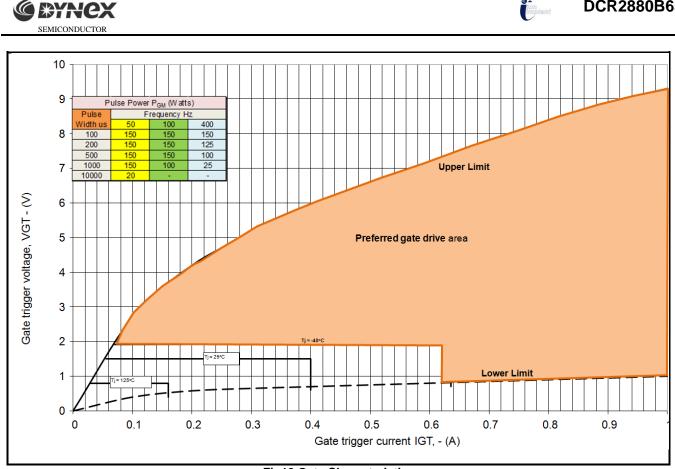


Fig.10 Reverse recovery charge

Fig.11 Reverse recovery current

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Fig12 Gate Characteristics

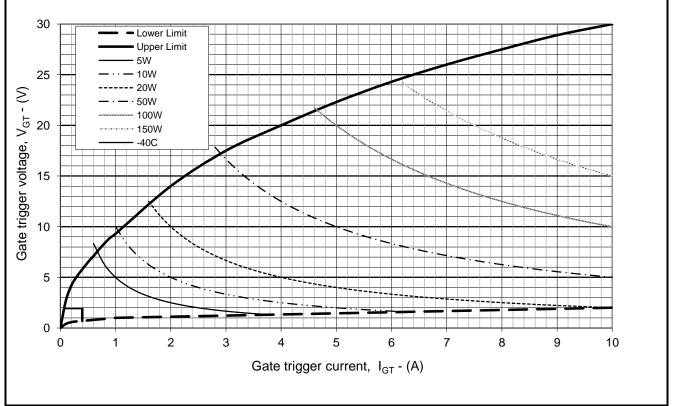


Fig. 13 Gate characteristics



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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

3rd ANGLE PROJECTION → ↔ → → → → → → → → → → → → → → → → →	[Maximum	
		Thickness	
	Device	(mm)	(mm)
HOLE Ø3.60 X 2.00 DEEP (IN BOTH	DCR5050B22	34.565	34.115
ELECTRODES)	DCR4590B28	34.64	34.19
	DCR3790B42	34.87	34.42
20° OFFSET (NOM.)	DCR3480B52	34.99	34.54
TO GATE TUBE	DCR2880B65	35.25	34.8
	DCR2400B85	35.61	35.16
CATHODE			
Clamping force: 76kN ± Lead length: 420mm Lead terminal connector: N	า		
Package outline type co	de: B		

Fig.14 Package outline





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DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire, LN6 3LF United Kingdom. Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901 Fax: +44 (0) 1522 500020 e-mail: power_solutions@dynexsemi.com

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